

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
-50V	6Ω @ $V_{GS} = -4 V$	-200mA
	8Ω @ $V_{GS} = -2.5V$	-160mA

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

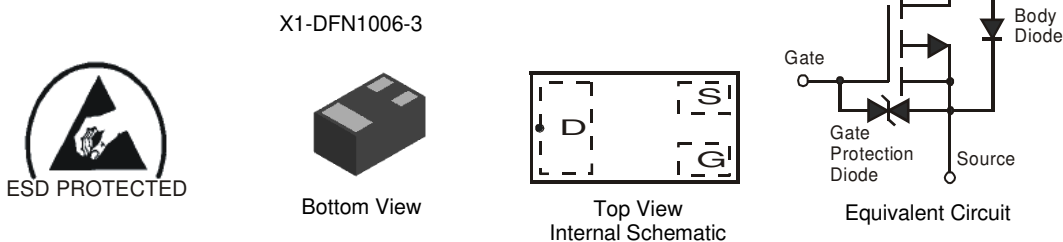
- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays

Features and Benefits

- Low On-Resistance
- ESD Protected Gate
- Low Input/Output Leakage
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: X1-DFN1006-3
- Package Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 **(e4)**
- Terminal Connections: See Diagram
- Weight: 0.001 grams (Approximate)


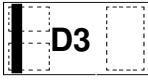
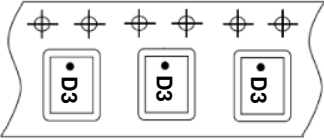
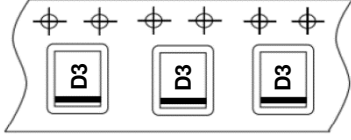

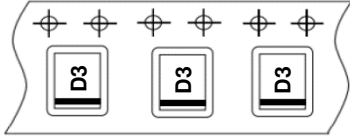


Ordering Information

Part Number	Package	Packing	
		Qty.	Carrier
DMP56D0UFB-7	X1-DFN1006-3	3,000	Tape & Reel
DMP56D0UFB-7B	X1-DFN1006-3	10,000	Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

DMP56D0UFB-7	 <p>Top View Dot Denotes Drain Side</p>  <p>Top View Bar Denotes Gate and Source Side</p> <p>From date code 1527 (YYWW), this changes to:</p>  
DMP56D0UFB-7B	 <p>Top View Bar Denotes Gate and Source Side</p> <p>D3 = Part Marking Code</p> 

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-50	V
Gate-Source Voltage	V_{GSS}	± 8	V
Drain Current (Note 5) Steady $T_A = +25^\circ\text{C}$	I_D	-200	mA
Pulsed Drain Current (Note 6)	I_{DM}	-700	mA

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	425	mW
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	275	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes: 5. Device mounted on FR-4 PCB. $t \leq 5$ sec.
 6. Pulse width $\leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-50	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-10	μA	$V_{DS} = -50V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 1	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	—	-1.2	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	4.6 6	6 8	Ω	$V_{GS} = -4.0V, I_D = -100mA$ $V_{GS} = -2.5V, I_D = -80mA$
Forward Transfer Admittance	$ Y_{fs} $	100	—	—	mS	$V_{DS} = -5V, I_D = -100mA$
Diode Forward Voltage (Note 7)	V_{SD}	—	-0.8	-1.2	V	$V_{GS} = 0V, I_S = -100mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	50.54	—	pF	$V_{DS} = -25V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	3.49	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	2.42	—	pF	
Gate Resistance	R_G	—	201	—	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ $f = 1.0MHz$
Total Gate Charge $V_{GS} = 4.5V$	Q_g	—	0.58	—	nC	$V_{DS} = -25V, I_D = -100mA$
Gate-Source Charge	Q_{gs}	—	0.09	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.14	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	4.46	—	nS	$V_{DD} = -30V, I_D = -0.27A,$ $V_{GEN} = -4V, R_{GEN} = 6\Omega$
Turn-On Rise Time	t_r	—	6.63	—	nS	
Turn-Off Delay Time	$t_{D(off)}$	—	21.9	—	nS	
Turn-Off Fall Time	t_f	—	15.0	—	nS	

Notes: 7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

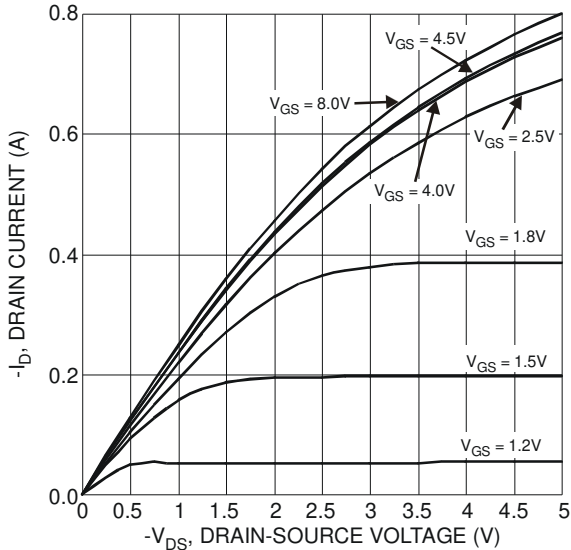


Figure 1 Typical Output Characteristics

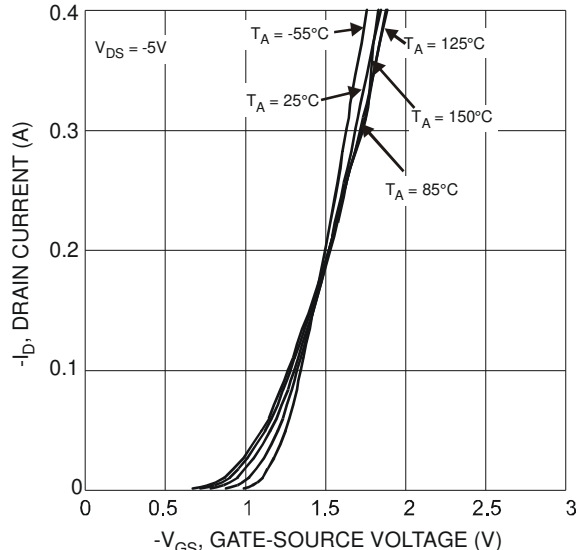


Figure 2 Typical Transfer Characteristics

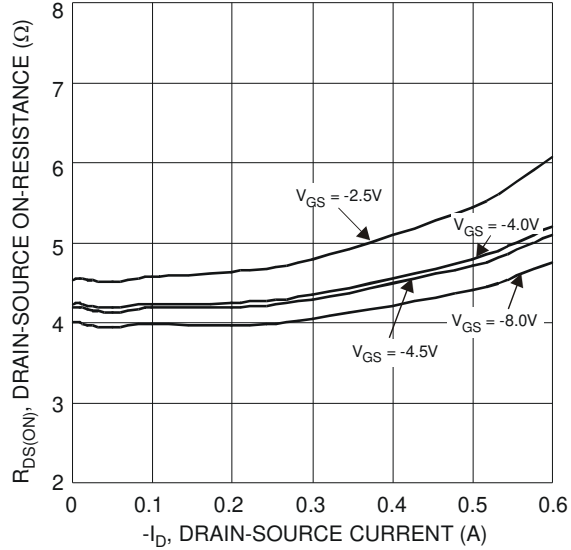


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

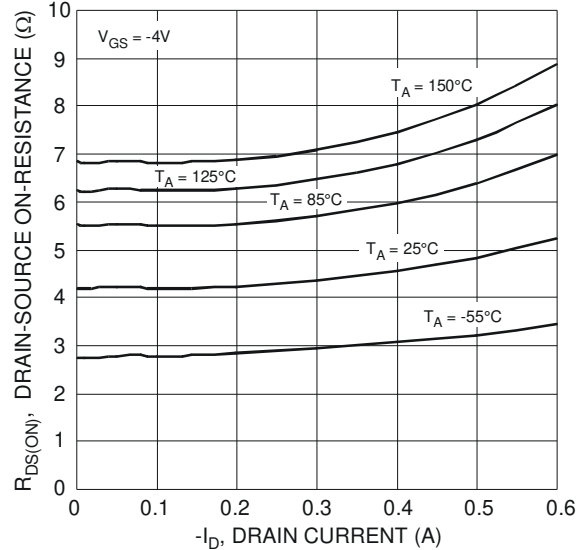


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

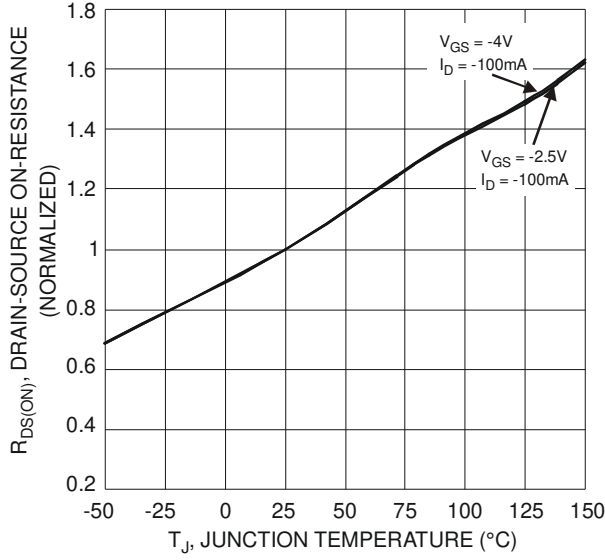


Figure 5 On-Resistance Variation with Temperature

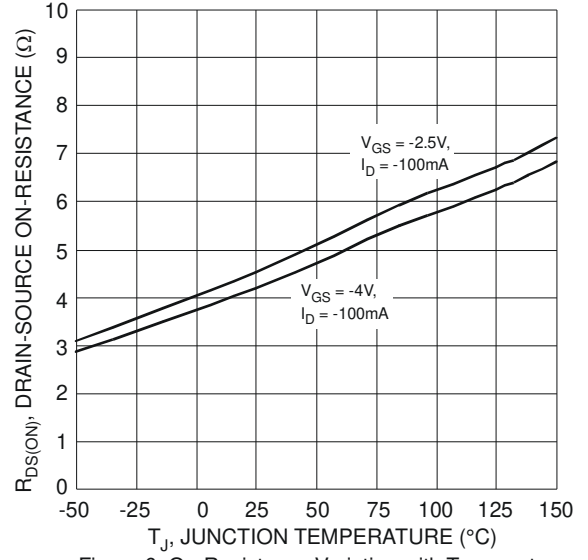


Figure 6 On-Resistance Variation with Temperature

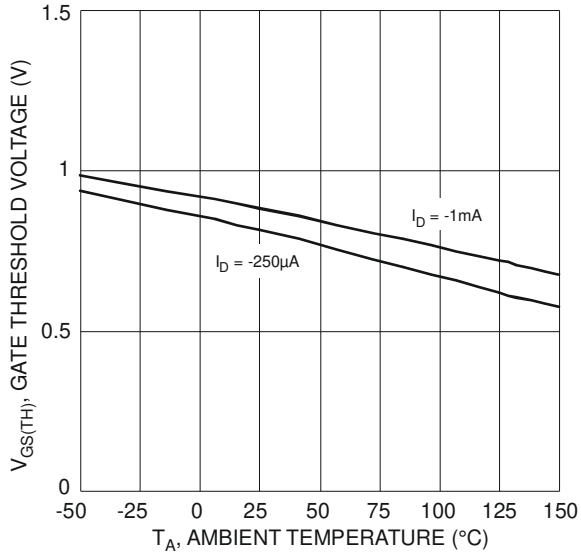


Figure 7 Gate Threshold Variation vs. Ambient Temperature

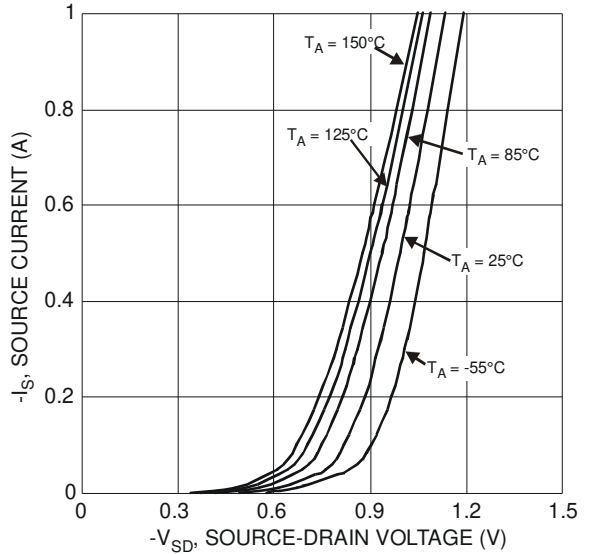


Figure 8 Diode Forward Voltage vs. Current

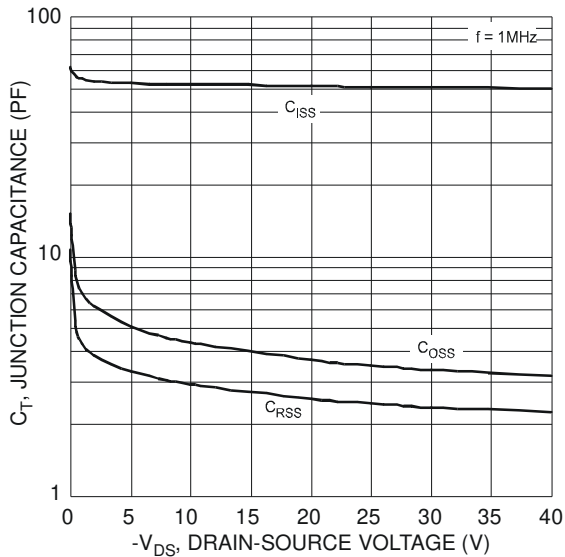


Figure 9 Typical Junction Capacitance

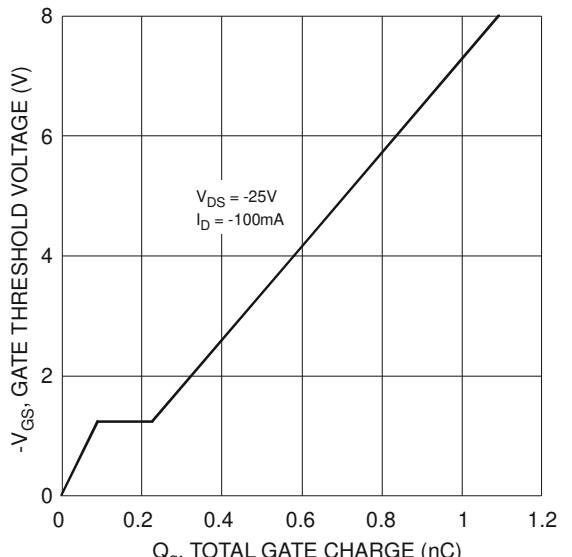
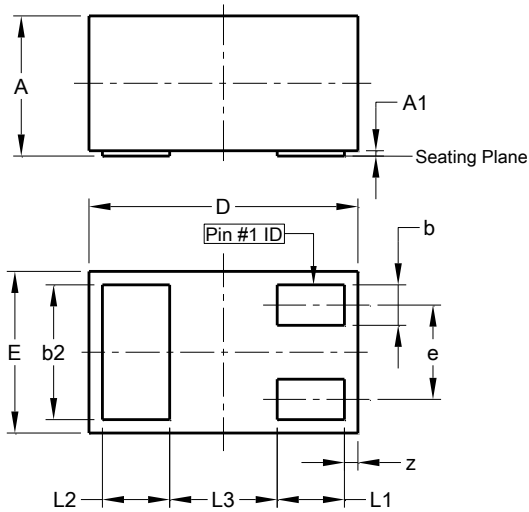


Figure 10 Gate Charge Characteristics

Package Outline Dimensions

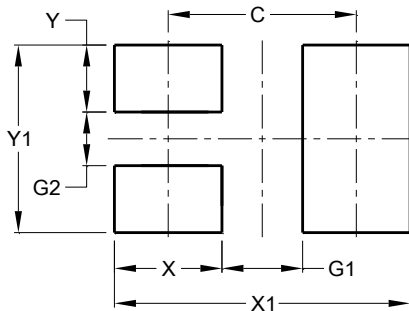
Please see <http://www.diodes.com/package-outlines.html> for the latest version.



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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